

Abstract of The Disclosure

With a high-speed nonvolatile phase change memory, reliability in respect of the number of refresh times is enhanced. In a memory cell forming area of a phase change memory using 5 a MISFET as a transistor for selection of memory cells, a phase change material layer of a memory cell comprising a resistor element, using a phase change material, is formed for common use. As a result, variation in shape and a change in composition of the phase change material, caused by isolation of memory cell 10 elements by etching, are reduced, thereby enhancing reliability of memory cells, in respect of the number of refresh times.